

Ion Getter Pumps CAS-2017

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Ion Pumps Pressure Range





Ion Pumps Structure



Body and Flange

- IGP are closed pumps: no foreline only inlet
- Whatever is pumped by IGP will remain into the IGP!
- Three different pumping elements but all of them are based on Penning Cell
- Penning cell is made of anode and cathode with high voltage applied
- That's why in a IGP we have ceramics insulators and HV feed-through



Penning Cell - Structure





Penning Cell – Electron Trap

• Combination of Electrical field and Mag field creates a trap for e-





Penning Cell - Ionization

- Gas molecules that enter into the cell can be ionized
 - resulting ions are attracted towards cathode
 - extracted e- is trapped as well
- The number of ions / sec (current) depends form pressure.

Ten times higher the pressure -> Ten times higher the current

- That's why IGP are used as pressure gauge
- At given Pressure, the current or better the discharge intensity I/P depends from:
 - Geometry of the cell
 - Number of cells
 - Mag field
 - Voltage





- Gas molecules that enter into the cell can be ionized and current is generated
- This current is almost linearly dependent from the pressure (with others parameters like cell geometry, number of cells, voltage, mag-field, fixed)
- Order of magnitude: a medium size pump (55 l/s) adsorbs about 1mA at 1*10-6 mbar
- @ 1*10-7 mbar the current will be roughly 0.1mA, etc...
- Lowest measurable pressure is limited by:
 - Resolution and precision of the power supply
 - Leakage current





- Resolution*
 - With a resolution of 100 nA the lowest measurable pressure is in the low 10-10 mbar. With a resolution of 10 nA we can read down to low 10-11 mbar range...

Leakage Current*

- Leakage current is mainly due to Electrons Field Emission from cathode
- This current does not depends from pressure
- Depends exponentially from voltage
- At low pressure the impact can be high



* example of a single element made of 53 cells with 1mA @ 1*10-6mbar



- Leakage Current*
 - Example-1
 - pump at 1*10-11mbar -> ionization current about 10nA
 - If we have a leakage of 100nA -> total current of 110nA
 - equivalent to 10-10 mbar! -> error of one decade!
 - Example-2
 - pump at 1*10-10mbar -> ionization current about 100nA
 - If we have a leakage of 100nA -> total current of 200nA
 - equivalent to 2*10-10 mbar! -> error of 50%!

* example of a single element made of 53 cells with 1mA @ 1*10-6mbar

How to minimize the leakage current effect? By reducing the voltage!

Field Emission is proportional to exponential of Voltage Let's see a real measurement example:



P/N: 919-1310s005 S/N: 207142





Pumping Mechanism

- Till now we have seen:
 - Penning cell -> trap of electrons
 - Ionization of gas molecules by interaction with e- cloud
 - Ionization current is proportional to pressure -> penning cell (and hence IGP) are used as pressure gauge

Now we have to see how an IGP pumps the gas

Pumping mechanism (and also efficiency) is dependent form gas type:

- Getterable gases
- Noble gases
- Hydrogen

In order to better pump one type of gas above, there are different configurations of IGP:

- Diode (penning cell structure seen till now)
- Noble diode
- Triode / Starcell



Pumping Mechanism – Getterable Gases

- lons (positively charged) are accelerated towards the cathodes.
- Impact sputter some Ti cathode atoms that stick on the anode surface
- Some of the ions accelerated towards the cathodes are neutralized and buried into the cathode
 - Not stable pumping!
- Some other gas molecules can hit the active titanium film are chemically trapped
 - Stable and permanent pumping









Saturation

Pumping at the cathodes is not permanent due to cathode's erosion

Previously implanted atoms are released

As a consequence, the net pumping speed decreases until an equilibrium condition between ion implantation and gas re-emission is reached.

At equilibrium the pump is called "saturated".

Saturated indicates stable operation mode of IGP, not the end of pump life !





IGP Saturation

Time to get to saturated condition depends from pressure

Higher the pressure -> higher the erosion rate -> faster the time to get to equilibrium (saturation)





Pumping Mechanism – Hydrogen

- Hydrogen is chemically reactive so it is pumped by the titanium film.
- Hydrogen has a high **solubility** in titanium (Ti acts as a "sponge"):

 \rightarrow diffusion into cathode after implantation.

- Titanium sputtering yield for hydrogen is very low, so only a small quantity of hydrogen is re-emitted by the cathode.
- Sputtering yield of Hydrogen is low
- Anyway pumping speed of H2 is roughly 50 to 100 % higher than for N2
- Pumps remains almost unsaturated for H2





Pumping Mechanism – Diode - Noble Gases

- Noble gases are not chemically active, so they are not chemisorbed by the titanium film at the anode
- We have two types of pumping mechanism of noble gases:
 - implanted into the cathode
 - this type of pumping is not stable and after saturation gas is released back → noble gas instability occurs.
 - Buried at anode
 - lons can be neutralized and reflected back ("bounced") from the cathodes as high energy neutrals
 - Hence noble gases can be implanted into the titanium sputtered on the anode:
 - \rightarrow stable pumping effect.





Typical Noble Gas Instability

Re-emission of Noble Gas implanted into he cathode happens suddenly

Pressure increases of one or few decades

After emission the gas is re-implanted into the cathode and stays there till the cathode erosion reach it and another re-emission (pressure increase) happens.

Periodicity of pressure peaks is a key indicator of NG instability

Time to show the instability depends from pressure -> need certain amount of gas pumped





Pumping Mechanism – Noble Diode Element

Goal: improve noble gases capacity and pumping speed

- One cathode made of Tantalum in order to increase the probability of reflecting noble gases as high energy neutrals.
- More stable and higher speed for noble gases with respect to diode.
- About the 80% of the speed for Nitrogen with respect to the diode.
- Reduced pumping speed and capacity for hydrogen.
- More expensive than diode.





Pumping Mechanism – Triode and Starcell Elements

Goal: improve noble gases pumping capacity and high hydrogen pump speed

- Cathode is made of Ti strips not anymore a flat plate like in the diode
- Anode is grounded, cathode is at negative voltage, Penning cell ionization mechanism still the same as in the diode
- New cathode shape increases the probability of reflecting noble gases as high ground
 -3-7kV
 ground
 -3-7kV
- Ions hitting the cathode with a glancing angle, have an increased probability to be emitted as neutrals
- Hence being buried in stable way at anode and on body





Pumping Mechanism – Triode and Starcell Elements

Stracell

- It is an improved version of the triode.
- Longer lifetime than diode element (titanium consumption is optimized).
- The shape of the small wings of the stars is optimized in order to maximize the reflection of neutrals (maximum pumping speed for noble gases).
- Pumping speed for nitrogen is about 80% with respect to the diode.
- Highest pumping speed and stability for noble gases.
- It can pump larger quantities of hydrogen than the noble diode, because both the cathodes are made out of titanium.







Pumping Mechanism - Elements Comparison

	StarCell	Diode	Noble Diode	
HYDROGEN	2	3	1	The Diode element shows a higher pumping speed for H ₂ than the Noble Diode since the H ₂ solubility in the tantalum cathode is lower than in a titanium cathode. StarCell elements combine good performance at higher pressures with enhanced capacity for H ₂ . It is worth noticing that hydrogen is the main residual gas in UHV.
ARGON, HELIUM	4	1	3	
WATER	2	3	2	Not considering physisorption phenomena, water can be pumped when separated into hydrogen and oxygen.
METHANE	3	2	3	The methane molecule (as well as other hydrocarbon molecules) is cracked and transformed into smaller getterable compounds (C, CH ₃ ,H).
NITROGEN	2	3	3	Diode and Noble Diode elements show a higher pumping speed for N_2 at low pressure while StarCell elements perform better at higher pressure, because the Penning discharge is betterconfined inside the element.
02, CO, CO2	2	3	3	As nitrogen, these are all getterable gases; same considerations as for N_2 .
poor 1	GOOD 2	EXCELLEN	ит <mark>3</mark> оц	JTSTANDING 4



Noble Gases Instability Element Comparison

Diode with Argon:

maximum capacity of about 2 hours at 1E-5 mbar of Argon;

200 h at 1E-7 mbar of Ar

2000 h at 1E-8 mbar of Ar

Noble Diode with Argon:

maximum capacity of about 10 hours at 1E-5 mbar of Argon;

1000 h at 1E-7 mbar of Ar 10000 h at 1E-8 mbar of Ar

Starcell with Argon:

maximum capacity of about 200 hours at 1E-5 mbar of Argon; 20000 h at 1E-7 mbar of Ar 200000 h at 1E-8 mbar of Ar





IGP Life Time

Reason that can end to IGP life end

- Vacuum leak
 - very unlikely, if not happen at the beginning will not happen long term
- Low Magnetic Field
 - can happen if suring bake out cross the Curie temperature usually very unlikely
- Noble Gases Instability
- Short Circuit
 - In case of complete metalization of insulators or due to cathode deformation – unlikely
- Leakage Current
 - If too high can affect the pressure indication
 - Does not affect the pumping speed!
- End of Titanium
 - When the erosion drilled completely the cathode -> no more sputtering





IGP Life Time

End of Titanium

- Time to end or drill the titanium depends from
 - Titanium thickness
 - Working pressure
 - Ten times higher the pressure -> ten times higer the sputtering rate
- Rough values
 - Diode 50'000 hours @ 1*10-6 mbar
 - Noble Diode 50'000 hours @ 1*10-6 mbar
 - Starcell 80'000 hours @ 1*10-6 mbar



Pumping Mechanism - Voltage

We have seen that by reducing the voltage, we reduce the lakage current but:

what happen to the pumping speed?

At lower pressure, the voltage that optimize the sputtering yeld (and hence the • pumping speed) is lower than at higher pressure - see graph below



This is due to the space charge effect:



Pumping Mechanism - Voltage

- Concentration of ions on cathode impact point that reduce the effective potential available for the ions acceleration
- Hence at 10-6mbar if we power the pump with 7kV, the available potential will be around 4kV
- In the 10-9 mbar the space charge is almost negligible and hence 3 kV are enough to optimize the sputtering yield





IGP – Pro and Cons

PRO

- Closed pump -> no risk of venting the system
- Do not need any baking pump (only at start-up)
- No contamination from the roughing line
- No moving parts, no lubricant, vibration free and contamination free
- Can withstand air inrush or improper use
- Maintenance free
- High reliability
- · Can work in high radiation areas

CONcerns

- Base Pressure can be limited by
 - self outgassing
 - contamination
 - cleaning and first bake out process are critichal
- Pumping Speed decreases with Pressure
- Particles emissions



Trends vs CONcerns – Cleaning and Outgassing

- Improve cleaning and self outgassing
 - Vacuum firing of Ti cathodes (well known)
 - Vacuum firing of anodes
 - Introduced since few years on all pumps
 - Anode is the second source of outgassing in a IGP
 - Started to introduce vacuum firing for the entire body

Vacuum Firing Furnace view All parts are first cleaned and all weldings done. After vacuum firing pump is assembled and finally baked-out.





Trends vs CONcerns – Cleaning and Outgassing

With vacuum firing

Standard process





Trends vs CONcerns – Pumping Speed at low Pressure

Classic

VS

Optimized

Classic magnetic field configuration (section of the pocket)



Optimized magnetic field configuration (section of the pump pocket)→ added magnets on the bottom









Trends vs CONcerns – Pumping Speed at low Pressure





Trends vs CONcerns – Particle Emission



- Plasma inside the IGP generates:
 - Ions
 - Electrons
 - Visible light
 - X-rays
 - Sputtered Ti

Most of these emissions can be stopped or drastically reduced by optical shields

Also for chanrged particles?



Some data from internal test on particle emission

TEST SET-UP PICTURES







lon pumps tested

1- Agilent Diode 40 l/s

2- Diode 40 l/s + Optimized Optical Shield







3- Competitor 45 L/S with Low Emission Element and shield





Results: Agilent Diode 40 vs Diode 40 + shield





Results: Agilent Diode 40 + shield vs Competitor



Confidentiality Label June 1, 2017







Thank You!

